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GR 98 P 1379 D

BOX AF

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By: Wm. S. Smith

Date: January 20, 2004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applic. No. : 09/885,553 Confirmation No. 6319
Applicant : Lars-Peter Heineck et al.
Filed : June 20, 2001
TC/A.U. : 2826
Examiner : Johannes P. Mondt
Title : MOS Transistor in a Single-Transistor Memory
Cell Having a Locally Thickened Gate Oxide

Docket No. : GR 98 P 1379 D

Customer No. : 24131

BOX AF

Hon. Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AMENDMENT under 37 C.F.R. § 1.116

S i r :

In response to the final Office action dated October 22, 2003,
please amend the above-identified application as follows:

Amendments to the Claims are reflected in the listing of
claims which begins on page 2 of this paper.

Remarks/Arguments begin on page 5 of this paper.